



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C	
1001/	220mΩ @ V _{GS} = 10V	1.6A	
100V	250mΩ @ $V_{GS} = 4.5V$	1.3A	

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

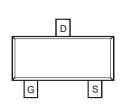
Load Switch

Mechanical Data

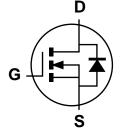
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.0072 grams (Approximate)







Pin Configuration



Equivalent Circuit

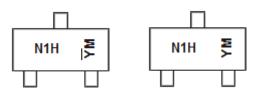
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H220L-7	Standard	SOT23	3000/Tape & Reel
DMN10H220L-13	Standard	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N1H = Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Kev

Year	201	3	2014		2015	20	16	2017		2018	2	2019
Code	Α		В		С)	Е		F		G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

April 2018



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units	
Drain-Source Voltage			V _{DSS}	100	V	
Gate-Source Voltage			V_{GSS}	±16	V	
Continuous Drain Current (Note 5) V 40V	(Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	1.6 1.3	А	
Continuous Drain Current (Note 5) V _{GS} = 10V (Note 5)		$T_A = +25$ °C $T_A = +70$ °C	I _D	1.4 1.1	А	
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	0.6	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%)		I _{DM}	8	Α	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	ם	1.3	W	
Total Fower Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	0.8		
Thermal Resistance, Junction to Ambient	(Note 6)	D	94	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{ÐJA}	177	G/ VV	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	1	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			_	220	mΩ	$V_{GS} = 10V, I_D = 1.6A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	_	_	250	11122	$V_{GS} = 4.5V, I_D = 1.3A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	401	_		V _{DS} = 25V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	22	_	pF		
Reverse Transfer Capacitance	Crss	_	17	_		I = IIVIHZ	
Gate Resistance	R_{g}	_	2.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	4.1	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	8.3	_	nC		
Gate-Source Charge	Q_{gs}	_	1.5	_	IIC	$V_{DS} = 50V, I_{D} = 1.6A$	
Gate-Drain Charge	Q_{gd}	_	2	_			
Turn-On Delay Time	t _{D(on)}	_	6.8	_			
Turn-On Rise Time	t _r	_	8.2	_		$V_{DS} = 50V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	_	7.9	_	ns	$R_G = 6.8\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _f	_	3.6	_			
Reverse Recovery Time	t _{rr}	_	17	_	ns	1 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	
Reverse Recovery Charge	Q_{rr}	_	9.8	_	nC	-I _F = 1.1A, di/dt =100A/μs	

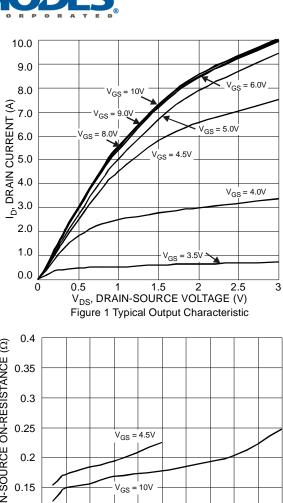
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

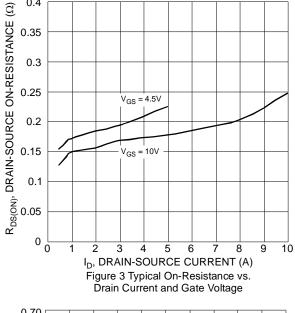
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.

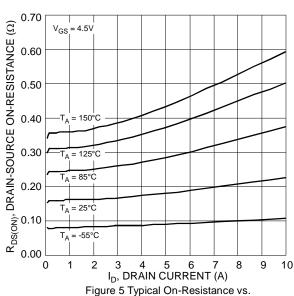
^{7 .}Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to production testing.

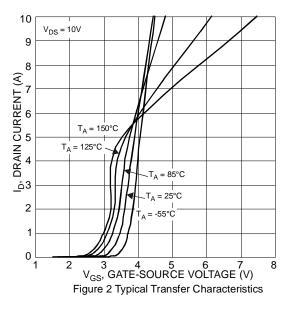


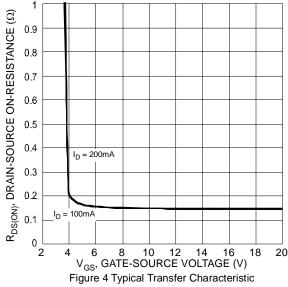






Drain Current and Temperature





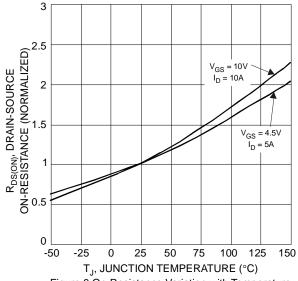
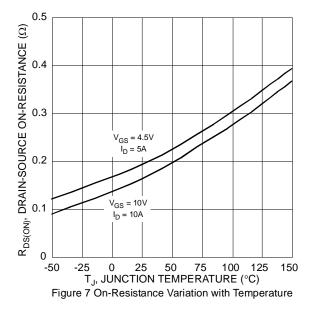
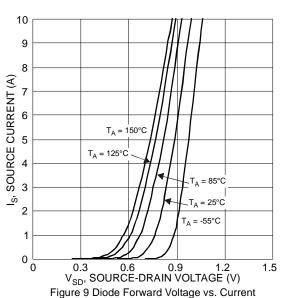
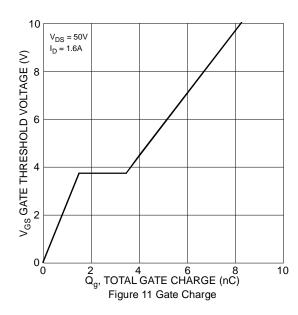


Figure 6 On-Resistance Variation with Temperature









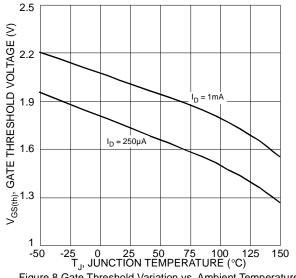
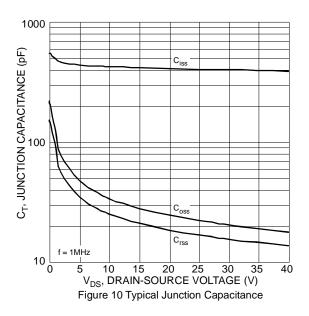
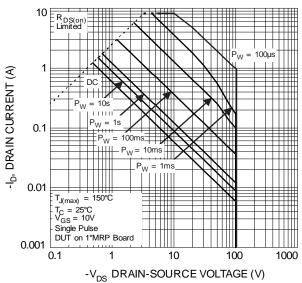


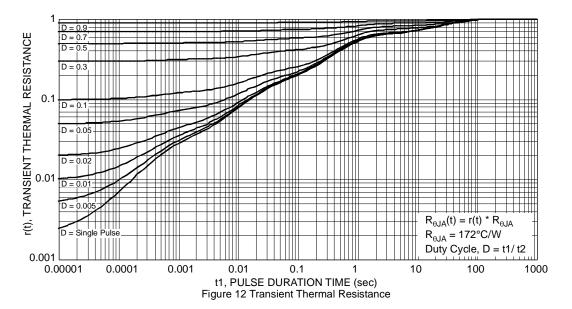
Figure 8 Gate Threshold Variation vs. Ambient Temperature





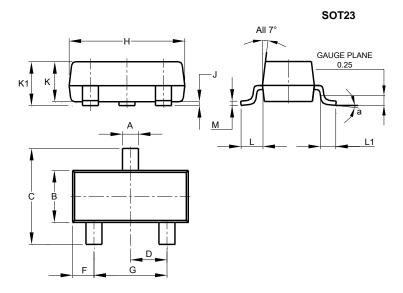
 ${}^{-}\mathrm{V}_{\mathrm{DS}}$ DRAIN-SOURCE VOLTAGE (V) Figure 12 SOA, Safe Operation Area





Package Outline Dimensions

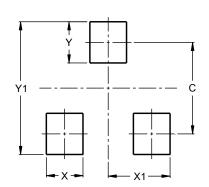
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K 1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9

2.9

Y1

SOT23



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